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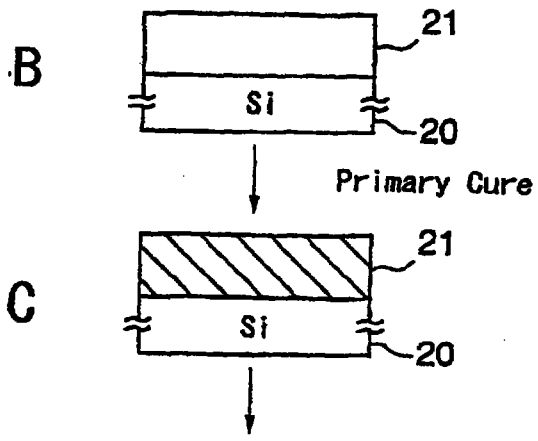
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(54) Title: FABRICATION PROCESS OF A SEMICONDUCTOR DEVICE



(57) Abstract: A method of fabricating a semiconductor device includes the steps of forming a first insulation film on a substrate by a spin-on process, applying a curing process to the first insulation film at a temperature of 380 - 500 C over a duration of 5 - 180 seconds, and forming a second insulation film on the first insulation film by a spin-on process.

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